國立臺灣海洋大學 103 學年度研究所碩士班招生考試試題

考試科目:電子學

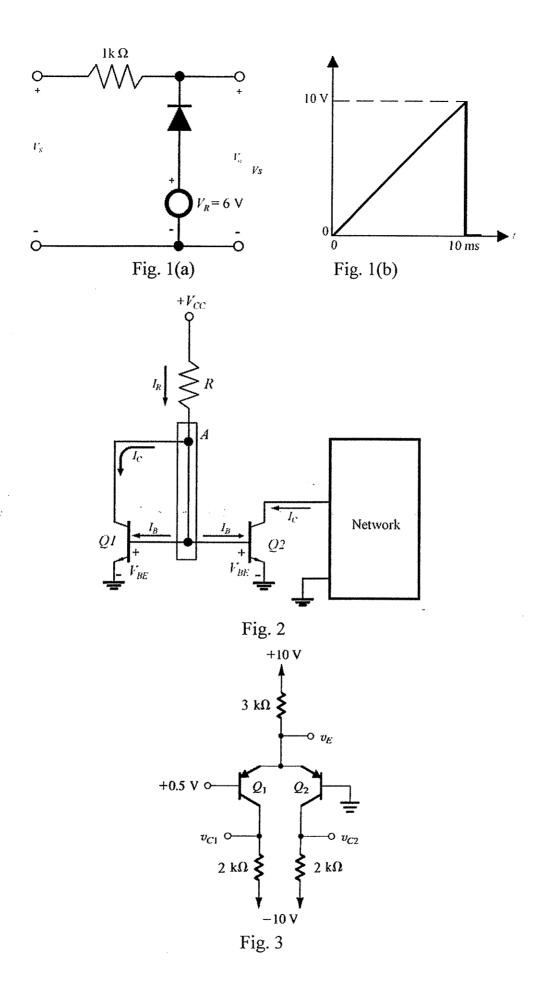
系所名稱:光電科學研究所碩士班不分組

*可使用計算器

1. 答案以橫式由左至右書寫。2. 請依題號順序作答。

1. An intrinsic silicon bar is 2 mm long and has a rectangular cross section $80 \times 100 \, \mu m$. At 300 K, determine the electric field intensity in the bar and the voltage across the bar when a steady current of 1 μA is measured. Note: the resistivity of this silicon bar is $2.3 \times 10^5 \, (\Omega \cdot cm)$. (10%)

- 2. For the circuit in Fig.1(a), for which the input voltage is the sawtooth waveform displayed in Fig.1(b), sketch (a) the transfer characteristic V_0 versus V_s and (b) the output waveform V_0 . The diode parameter are $R_f = 10 \Omega$, $V_r = 0.6 V$, and $I_s = 0$. (20%)
- 3. Explain an *npn* transistor operation mode when consider with the (a) emitter-base and collector-base junction bias. (b) If the transistor is operated under forward active mode with the base-collector are short circuit, determined the *common-base forward* short-circuit current gain α_F when I_E and I_C values are 2 X 10⁻³ A and 5 X 10⁻³ A. (10%)
- 4. The circuit shown in Fig. 2 is a current mirror. The transistors QI and Q2 are identical, (a) Determine I_C in terms of circuit parameters. (b) Evaluate I_C for $V_{CC} = 10$ V, $R = 10 \text{ k}\Omega$ and $\beta_F = 100$. (10%)
- 5. For the circuit in Fig. 3, find the values of v_E , v_{C1} , and v_{C2} . Assume that $|V_{BE}|$ of a conducting transistor is 0.7 V and that common-base current gain $\alpha \simeq 1$. (12%)
- 6. For the circuit in Fig. 4, the NMOS and PMOS transistors are matched with $k'_n(W_n/L_n) = k'_p(W_p/L_p) = 0.6 \text{ mA/V}^2$ and $V_{tn} = -V_{tP} = 1 \text{ V}$. Find the drain current i_{DN} , i_{DP} and the voltage v_o for $v_I = +5 \text{ V}$ and -5 V. Neglect the channel-length modulation effect for both devices (i.e., assume that $\lambda = 0$). (18%)
- 7. For the circuit in Fig. 5, let $R_1 = 2 \text{ k}\Omega$ and $R_2 = 5 \text{ k}\Omega$. Find v_O and the voltage at the amplifier output v_A for $v_I = +2 \text{ V}$, -20 mV, and -0.2 V. Assume the op amp to be ideal with saturation voltages of $\pm 12 \text{ V}$. The diodes have 0.7-V voltage drops at 1 mA, and the voltage drop changes by 0.1 V per decade of current change. (20%)



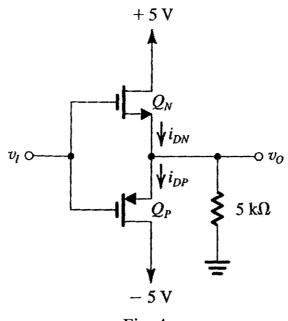


Fig. 4

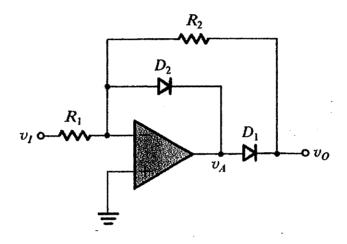


Fig. 5